

EV 182656601

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial Number 09/292,132
Filing Date April 14, 1999
Inventor Salman Akram et al.
Assignee Micron Technology, Inc.
Group Art Number 2812
Examiner S. Mulpuri
Attorney's Docket No. MI22-1171
Title: Methods of Forming a Transistor Gate

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT


Reference -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether the submitted reference is prior art.

Respectfully submitted,

Dated: 1-02-03

Attorney:


D. Brent Kenady
Reg. #40,045

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Form PTO-1120		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M22-1171		SERIAL NO. 09/292,132	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Simeon Abram et al.			
				FILING DATE April 14, 1999		GROUP 2812	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AL						
	AM						
	AN						
	AO						
	AP						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR		Wolf, Ph. D., Stanley, "Siscon Processing for the VLSI Era - Volume 2: Process Integration," ©1990 Lattice Press, pages 212-213.				
	AS						
	AT						
EXAMINER				DATE CONSIDERED			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							